Pb Free Plating Product

SFF1004GA/SFF1006GA/SFF1008GA





10 Ampere Isolated Dual Common Anode Fast Recovery Half Bridge Rectifiers

Features

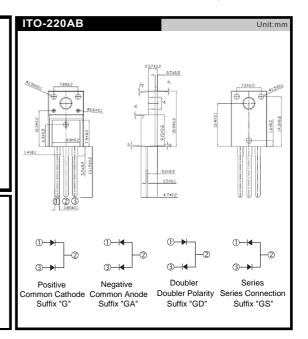
- ★ Latest GPP technology with super fast recovery time
- ★ Low forward voltage drop
- ★ High current capability
- ★ Low reverse leakage current
- * High surge current capability

Application

- ★ Automotive Inverters and Solar Inverters
- ★ Plating Power Supply,SMPS,EPS and UPS
- ★ Car Audio Amplifiers and Sound Device Systems

Mechanical Data

- ★ Case: Fully Insulated Molding TO-220F
- ★ Epoxy: UL 94V-0 rate flame retardant
- Terminals: Solderable per MIL-STD-202 method 208
- ★ Polarity: As marked on diode body
- **★** Mounting position: Any
- ★ Weight: 2.0 gram approximately



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

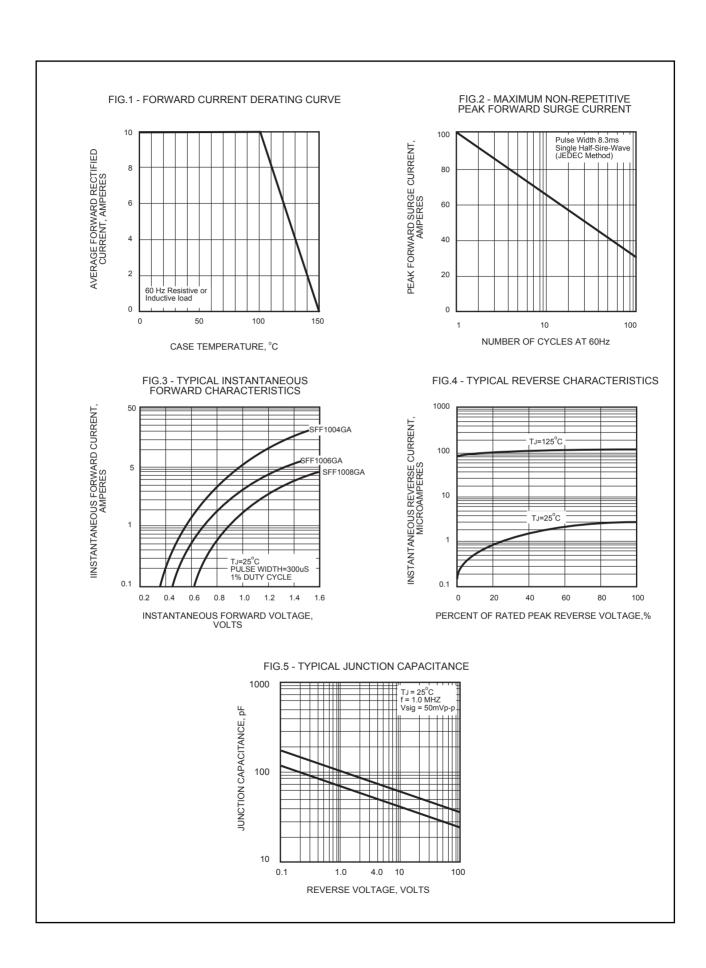
For capacitive load, derate current by 20%.

	SYMBOL	SFF1004GA	SFF1006GA	SFF1008GA	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	200	400	600	V
Maximum RMS Voltage	VRMS	140	280	420	V
Maximum DC Blocking Voltage	VDC	200	400	600	V
Maximum Average Forward Rectified Current Tc=100°C	IF(AV)	10.0			А
Peak Forward Surge Current, 8.3ms single Half sine-wave superimposed on rated load (JEDEC method)	IFSM	100			А
Maximum Instantaneous Forward Voltage @ 5.0 A	VF	0.98	1.3	1.7	V
Maximum DC Reverse Current @TJ=25°C At Rated DC Blocking Voltage @TJ=125°C	lR	5.0 100			uA uA
Maximum Reverse Recovery Time (Note 1)	Trr	35			nS
Typical junction Capacitance (Note 2)	CJ	65			pF
Typical Thermal Resistance (Note 3)	Raic	2.2			°C/W
Operating Junction and Storage Temperature Range	TJ, TSTG	-55 to +150			°C

NOTES: (1) Reverse recovery test conditions $I_F = 0.5A$, $I_R = 1.0A$, $I_{TT} = 0.25A$.

- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts DC.
- (3) Thermal Resistance junction to case.

Edition:20210603 Page 1/2



Edition:20210603 Page 2/2